

Thematic course: Hydrochemical synthesis of metal chalcogenide films. Part 14.

X-ray photoelectronic spectroscopy of the chemical bath deposited films CuGaSe₂

© Vyacheslav F. Markov,^{1*} Stanislav S. Tulenin,¹ Ekaterina A. Fedorova,¹
Elena V. Levashova,¹ Larisa N. Maskaeva,²⁺ and Mikhail V. Kuznetsov³

¹ Chair Physical and Colloidal Chemistry. The Ural Federal University of a Name of the First President of Russia B.N. Yeltsin. Mira St., 19. Ekaterinburg, 620002. Sverdlovsk area. Russia.
Phone: +7 (343) 375-93-18. E-mail: mln@ural.ru

² Chair of Chemistry and Burning Processes. Ural Institute GPS of the Ministry of Emergency Measures of Russia. Mira St., 22. Ekaterinburg, 620022. Russia. Phone: +7 (343) 360-81-68.

E-mail: v.f.markov@ustu.ru

³ Institute of Chemistry of a Solid State. The Ural Branch of the Russian Academy of Sciences. Pervomaiskay St., 91. Ekaterinburg, 620990. Russia. Phone: +7 (343) 362-33-56.

E-mail: kuznetsov@ihim.uran.ru

*Supervising author; +Corresponding author

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Abstract

Boundary conditions of formation Cu₂Se and In₂Se₃ and also their hydroxides defines by means of calculation of ionic equilibrium with using of thermodynamic constants for systems "nitrate gallium – copper(I) chloride – selenourea" and "nitrate gallium – copper(I) chloride – sodium selenosulphate" accounting the formation of crystal nucleus with critical radii.

Experimental date on distributions and atomic rations of elements in a chemical bath deposited thin films Cu₂Se–Ga₂Se₃ was discussed by means of the X-ray photoelectronic spectroscopy method.